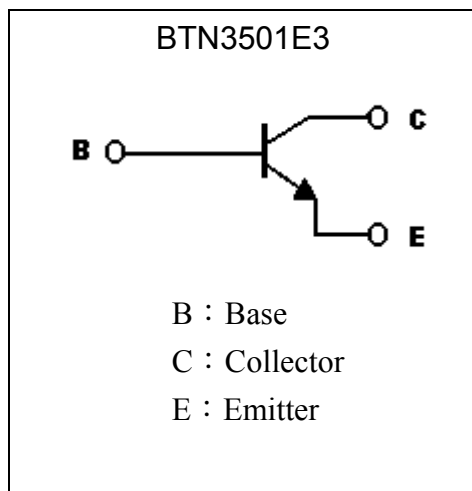
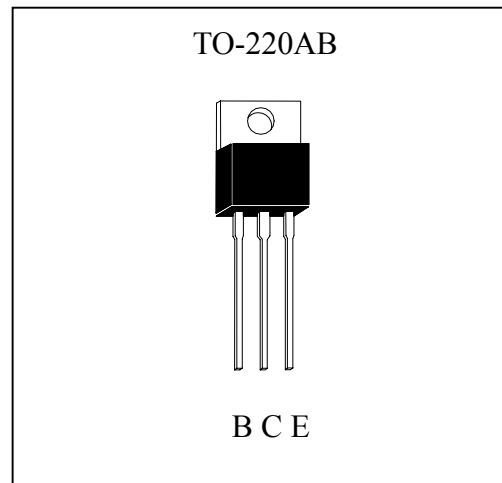


Low Vcesat NPN Epitaxial Planar Transistor

BTN3501E3

Features

- Low $V_{CE(sat)}$
- High BV_{CEO}
- Excellent current gain characteristics

Symbol

Outline

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current (DC)	I_C	10	A
Collector Current (Pulse)	I_{CP}	20 (Note 1)	
Power Dissipation @ $T_A=25^\circ\text{C}$	P_D	2	W
Power Dissipation @ $T_c=25^\circ\text{C}$	P_D	50	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.5	$^\circ\text{C}/\text{W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~+150	$^\circ\text{C}$

Note : 1. Single Pulse , $P_w \leq 380\mu\text{s}$, $Duty \leq 2\%$.



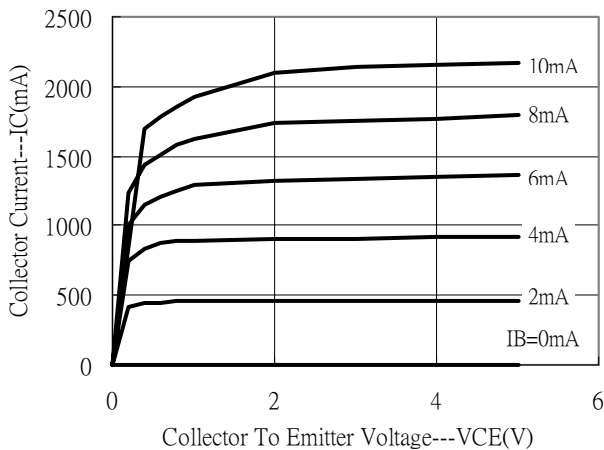
Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
$BV_{CEO(SUS)}$	80	-	-	V	$I_C=30mA, I_B=0$
I_{CES}	-	-	10	μA	$V_{CE}=80V, V_{BE}=0$
I_{EBO}	-	-	50	μA	$V_{EB}=5V, I_C=0$
* $V_{CE(sat)}$	-	0.3	0.6	V	$I_C=8A, I_B=0.4A$
* $V_{BE(sat)}$	-	1.0	1.5	V	$I_C=8A, I_B=0.8A$
* h_{FE}	60	-	-	-	$V_{CE}=1V, I_C=2A$
* h_{FE}	40	-	-	-	$V_{CE}=1V, I_C=4A$
f_T	-	50	-	MHz	$V_{CE}=6V, I_C=500mA, f=20MHz$
Cob	-	130	-	pF	$V_{CB}=10V, f=1MHz$

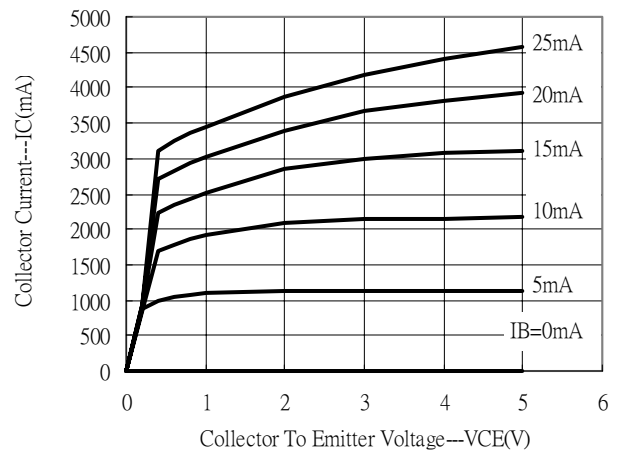
*Pulse Test : Pulse Width $\leq 380\mu s$, Duty Cycle $\leq 2\%$

Characteristic Curves

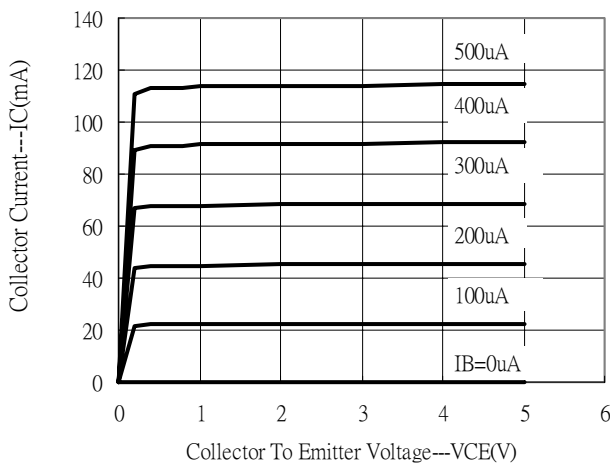
Grounded Emitter Output Characteristics



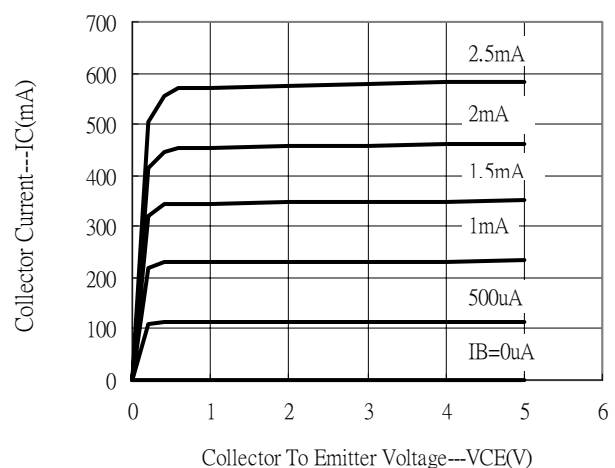
Grounded Emitter Output Characteristics



Grounded Emitter Output Characteristics

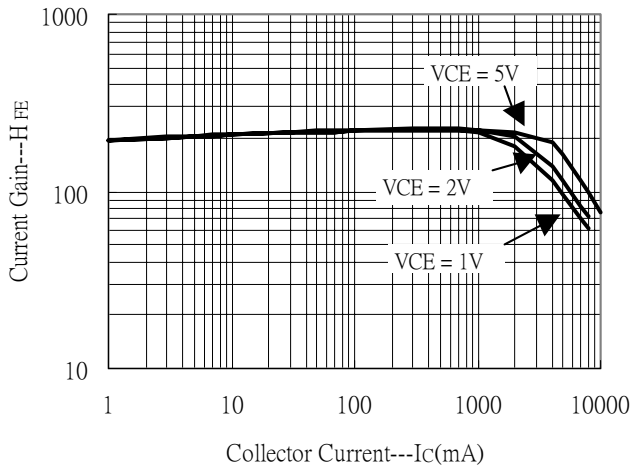


Grounded Emitter Output Characteristics

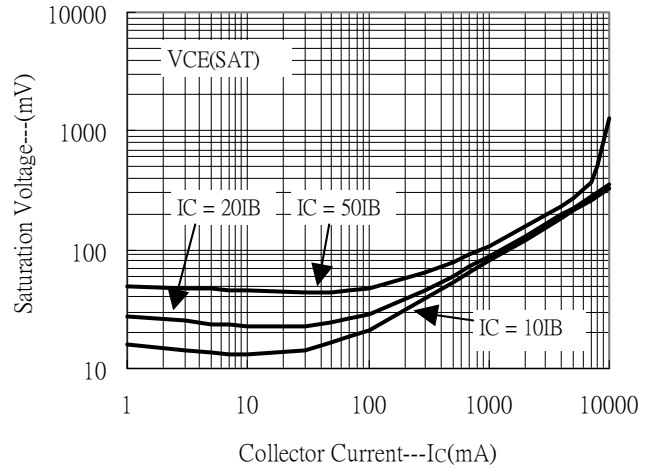




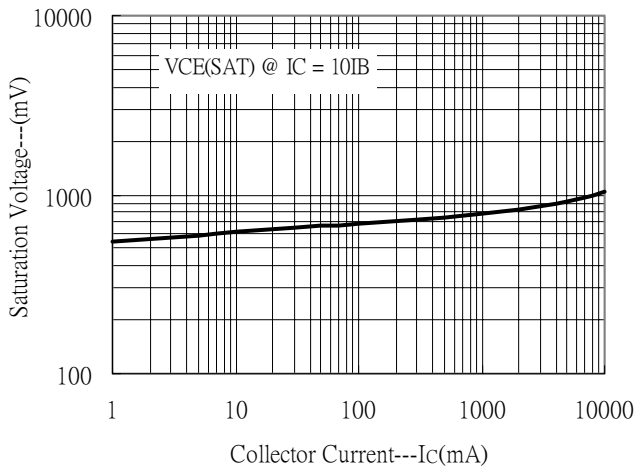
Current Gain vs Collector Current



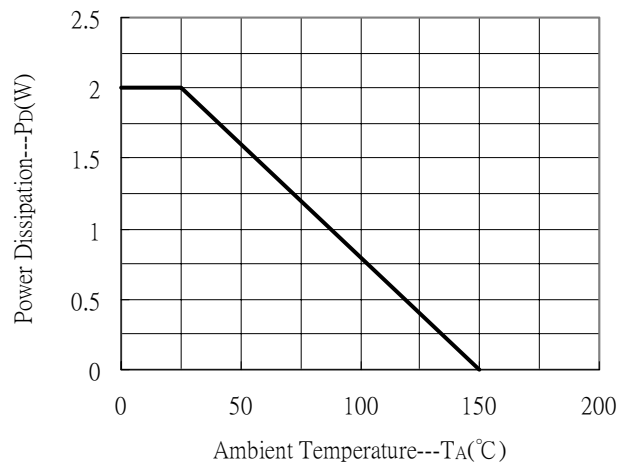
Saturation Voltage vs Collector Current



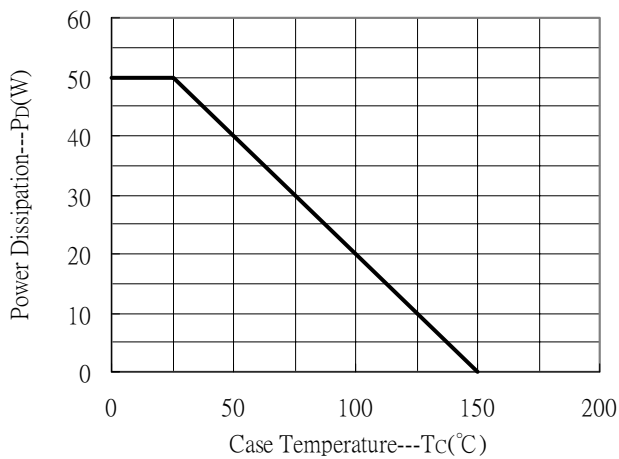
Saturation Voltage vs Collector Current



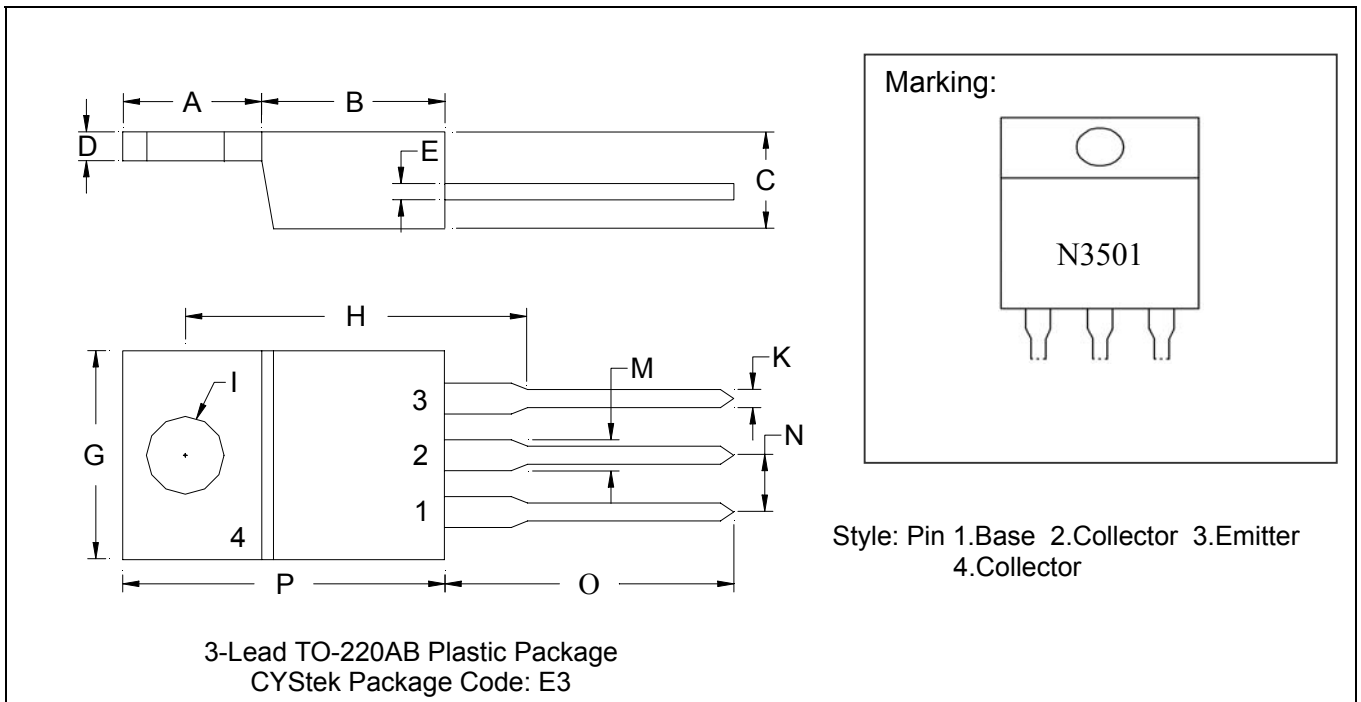
Power Derating Curve



Power Derating Curve



TO-220AB Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.2197	0.2949	5.58	7.49	I	-	*0.1508	-	*3.83
B	0.3299	0.3504	8.38	8.90	K	0.0295	0.0374	0.75	0.95
C	0.1732	0.185	4.40	4.70	M	0.0449	0.0551	1.14	1.40
D	0.0453	0.0547	1.15	1.39	N	-	*0.1000	-	*2.54
E	0.0138	0.0236	0.35	0.60	O	0.5000	0.5618	12.70	14.27
G	0.3803	0.4047	9.66	10.28	P	0.5701	0.6248	14.48	15.87
H	-	*0.6398	-	*16.25					

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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